

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	3	"20050174845"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L3	2	WO near2 "9607300"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L4	1	1996-160638.NRAN.	DERWENT	ADJ	ON	2010/06/04 18:10
L5	18	"5195010"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L6	5633	heat\$3 with silicon with (voltage or current)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L7	317	(chang\$3 or alter\$3 or convert\$3) with silicon with (current or voltage) with heat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L8	2	(chang\$3 or alter\$3 or convert\$3) with silicon with (current or voltage) with heat\$3 with (source and drain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L9	15	(chang\$3 or alter\$3 or convert\$3) with ((poly silicon) or (polycrystalline silicon) or (poly\$1\$1)) with (current or voltage) with heat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10

L10	10	(chang\$3 or alter\$3 or convert\$3) with (SiGe or (silicon germanium)) with (current or voltage) with heat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L11	662	(MURAKAMI near2 SHIGERU).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L12	29	(YAMAGATA near2 YASUJI ).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L13	4485	(257/16,49,52,59).CQLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
L14	724	(257/64,68).CQLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
L15	1281	(257/770-772).CQLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
L16	390	(438/153).CQLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
L17	1654	(438/166).CQLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
L18	3009	(438/238-239).CQLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
L19	1476	(438/478).CQLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
L20	3	"20020126108"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L21	13807	((write near2 once) memory) or (WOM)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L22	12417	(semiconductor (film or material)) same ((amorphous silicon) or (a \$1silicon) or (a\$1Si))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10

L23	63	L21 and L22	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L24	10427	((write near2 once) memory) or (one time programmable) or (OTP)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L25	24817	(semiconductor (film or material)) same ((amorphous silicon) or (a \$1silicon) or (a\$1Si) or (SiGe) or (Silicon Germanium))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L26	238	L24 and L25	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
L27	291	((gate or dielectric or insulat \$3) and (semiconductor) ) and (((write near2 once) memory) or (one time programmable) or (OTP)). ti.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
L28	8	((thin film transistor) or (thinfilm transistor) or TFT) and L27	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
L29	1	jp "56044198"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
L30	185	"20030198077" "20050098811" "20050194645" "20060054894" "20060175648" "5850090" "5994730" "6384439" "6465828" "6555420" "6576948" "6583490" "6690031" "6958740" "7113420" "7368343"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/04 18:11

L31	53854	voltage same increas\$3 same resistance same (semiconductor (film or material or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/04 18:11
L32	51204	((write near2 once) memory) or (one time programmable) or (OTP) and L31	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/04 18:11
L33	2657	((thin film transistor) or (thinfilm transistor) or TFT) and L32	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
L34	136	memory.ti. and L33	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
L35	1278	((apply\$3 or programm\$4 or operat\$3) near3 voltage) same (alter\$3 or chang\$3 or convert\$3) same (semiconductor (film or material or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
L36	229	((thin film transistor) or (thinfilm transistor) or TFT) and L35	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
L37	10	((write near2 once) memory) or (one time programmable) or (OTP) and L36	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
L38	2702	voltage same increas\$3 same resistance same (semiconductor (film or material or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11

L39	20	((write near2 once memory) or (one time programmable) or (OTP)) and L38	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
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**EAST Search History (Interference)**

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